

SKM100GB12V



SEMITRANS® 2

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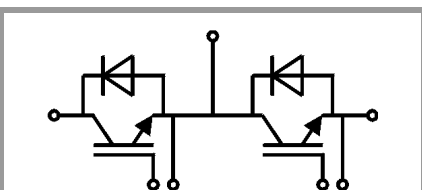
Target Data

Features

- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_{Cnom}
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders at fsw up to 20 kHz



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V_{CES}			1200	V
I_C	$T_j = 175\text{ °C}$	$T_c = 25\text{ °C}$	155	A
		$T_c = 80\text{ °C}$	117	A
I_{Cnom}			100	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		300	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 720\text{ V}$	$T_j = 125\text{ °C}$	10	μs
	$V_{GE} \leq 20\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
T_j			-40 ... 175	°C
Inverse diode				
I_F	$T_j = 175\text{ °C}$	$T_c = 25\text{ °C}$	121	A
		$T_c = 80\text{ °C}$	91	A
I_{Fnom}			100	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		300	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25\text{ °C}$		550	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			200	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	$I_C = 100\text{ A}$	$T_j = 25\text{ °C}$	1.75	2.2		V
		$T_j = 150\text{ °C}$	2.2	2.65		V
V_{CE0}		$T_j = 25\text{ °C}$	0.94	1.25		V
		$T_j = 150\text{ °C}$	0.88	1.22		V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	8.1	9.5		mΩ
		$T_j = 150\text{ °C}$	13.2	14.3		mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 4\text{ mA}$		6	6.5	7	V
I_{CES}	$V_{GE} = 0\text{ V}$	$T_j = 25\text{ °C}$	0.1	0.3		mA
		$T_j = 150\text{ °C}$				mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$	6.01			nF
C_{oes}		$f = 1\text{ MHz}$	0.59			nF
C_{res}		$f = 1\text{ MHz}$	0.589			nF
Q_G			1150			nC
R_{Gint}			7.5			Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150\text{ °C}$	294			ns
t_r	$I_C = 100\text{ A}$	$T_j = 150\text{ °C}$	38			ns
		$V_{GE} = \pm 15\text{ V}$	10			mJ
E_{on}	$R_{Gon} = 1\text{ }\Omega$	$T_j = 150\text{ °C}$	418			ns
$t_{d(off)}$	$R_{Goff} = 1\text{ }\Omega$	$T_j = 150\text{ °C}$	62			ns
t_f	$di/dt_{on} = 3230\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$	8			mJ
E_{off}	$di/dt_{off} = 1330\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$				mJ
$R_{th(j-c)}$	per IGBT			0.27		K/W

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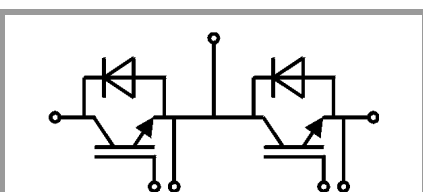
Features

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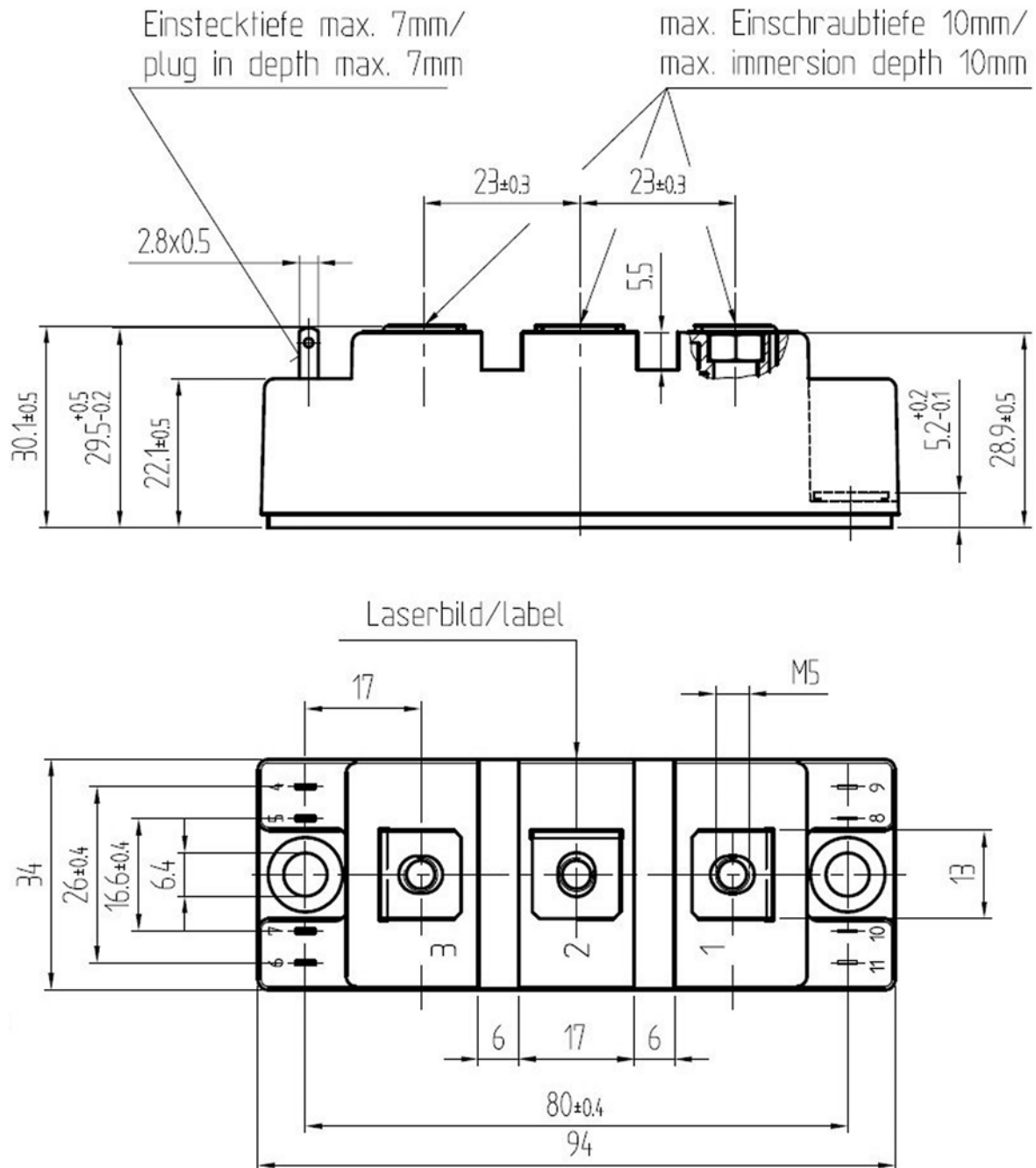
- AC inverter drives
- UPS
- Electronic welders at fsw up to 20 kHz

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 100 \text{ A}$ $V_{GE} = 0 \text{ V}$ chip	$T_j = 25 \text{ °C}$		2.2	2.5	V
		$T_j = 150 \text{ °C}$		2.1	2.5	V
V_{F0}		$T_j = 25 \text{ °C}$		1.3	1.5	V
		$T_j = 150 \text{ °C}$		0.9	1.1	V
r_F		$T_j = 25 \text{ °C}$		9.0	10.2	mΩ
		$T_j = 150 \text{ °C}$		12.5	13.7	mΩ
I_{RRM}	$I_F = 100 \text{ A}$	$T_j = 150 \text{ °C}$		54		A
Q_{rr}	$di/dt_{off} = 1600 \text{ A/}\mu\text{s}$	$T_j = 150 \text{ °C}$		15.7		μC
E_{rr}	$V_{GE} = \pm 15 \text{ V}$ $V_{CC} = 600 \text{ V}$	$T_j = 150 \text{ °C}$		5.9		mJ
$R_{th(j-c)}$	per diode				0.48	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_C = 25 \text{ °C}$		0.65		mΩ
		$T_C = 125 \text{ °C}$		1		mΩ
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g

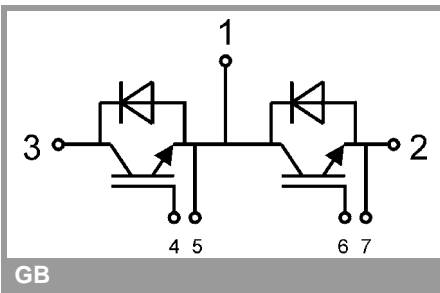


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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.